

1 2インチ N 型 SiC ウエハー（暫定仕様）



Parameter	Unit	Specification Value
Diameter	mm	300±0.25
Thickness	μm	700 ± 100
Surface Orientation		4 °toward<11-20>± 0.5°
Primary Flat Length		Notch
Notch Depth	mm	1 ~ 1.5mm
Micropipe Density	cm ²	≤ 0.2
TTV	μm	≤10
Surface Roughness		Si Face Ra≤ 0.5 nm, C Face Ra≤ 5 nm
Edge Chips		No chipping with depth exceeding 1mm
Laser marking		As per SEMI Standard
Polytype Area by polarized light		None permitted
Cracks by high-intensity light		None permitted
Packaging		Single Wafer Container outer packing: no damage, no air leakage.